

Excellent Integrated System Limited

Stocking Distributor

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Vishay/Siliconix SI7886ADP-T1-E3

For any questions, you can email us directly: sales@integrated-circuit.com







Si7886ADP

Vishay Siliconix

N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}(\Omega)$ $I_{D}(A)$		Q _g (Typ.)		
30	0.0040 at V _{GS} = 10 V	25	47		
	0.0048 at V _{GS} = 4.5 V	23	4/		

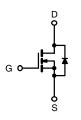
· Halogen-free available

- TrenchFET® Power MOSFET
- Optimized for "Low Side" Synchronous **Rectifier Operation**
- New Low Thermal Resistance PowerPAK® Package with Low 1.07 mm Profile
- 100 % R_g Tested

FEATURES

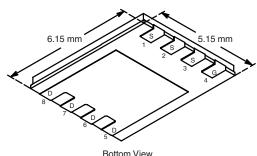
FEATURES

- DC/DC Converters
- Synchronous Rectifiers



N-Channel MOSFET

PowerPAK SO-8



Ordering Information: Si7886ADP-T1-E3 (Lead (Pb)-free)

Si7886ADP-T1-GE3 (Lead (Pb)-free and Halogen-free)

Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V_{DS}	30		V
Gate-Source Voltage		V_{GS}	± 12		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 25 °C	I_	25	15	
	T _A = 70 °C	I _D	20	12	
Pulsed Drain Current (10 µs Pulse Width)		I _{DM}	60		Α
Continuous Source Current (Diode Conduction) ^a		I _S	4.5	1.6	
Avalanche Current	L = 0.1 mH	I _{AS}	50		
Single Pulse Avalanche Energy	L = 0.1 IIII1	E _{AS}	125		mJ
Maximum Power Dissipation ^a	T _A = 25 °C	P _D	5.4	1.9	W
	T _A = 70 °C	טי	3.4	1.2	VV
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C
Soldering Recommendations (Peak Temperature) ^{b, c}		_	260		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^a	t ≤ 10 s	- R _{thJA}	18	23		
Maximum Junction-to-Ambient	Steady State		50	65	°C/W	
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	1.0	1.5		

- a. Surface Mounted on 1" x 1" FR4 board.
- b. See Solder Profile (http://www.vishay.com/ppg?73257). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- c. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

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Datasheet of SI7886ADP-T1-E3 - MOSFET N-CH 30V 15A PPAK SO-8

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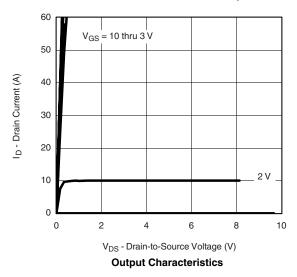
Parameter	Symbol Test Condition Min		Min.	lin. Typ.	Max.	Unit
Static					L L	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	0.6	1	1.5	V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS} -	V _{DS} = 30 V, V _{GS} = 0 V			1	
		$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$	30 V, V _{GS} = 0 V, T _J = 55 °C			μΑ
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	30			Α
Drain-Source On-State Resistance ^a	D	V _{GS} = 10 V, I _D = 25 A	0.0032 0.0		0.0040	0
	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 23 \text{ A}$		0.0037	0.0048	Ω
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 25 A	Α			S
Diode Forward Voltage ^a	V_{SD}	I _S = 2.9 A, V _{GS} = 0 V		0.7	1.1	V
Dynamic ^b	· · · · · · · · · · · · · · · · · · ·		*		'	
Input Capacitance	C _{iss}			6450		pF
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{SS} = 0 \text{ V}, f = 1 \text{ kHz}$		873		
Reverse Transfer Capacitance	C _{rss}			402		
Total Gate Charge	Qg			47	60	nC
Gate-Source Charge	Q _{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 25 \text{ A}$		12.5		
Gate-Drain Charge	Q_{gd}			9.0		
Gate Resistance	R_g		0.5	1.0	1.5	Ω
Turn-On Delay Time	t _{d(on)}			17	30	
Rise Time	t _r	V_{DD} = 15 V, R_L = 15 Ω		14	25	ns
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ 1.0 A, V_{GEN} = 10 V, R_G = 6 Ω		158	230	
Fall Time	t _f			43	65	
Source-Drain Reverse Recovery Time	t _{rr}	$I_F = 2.9 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$		50	80	

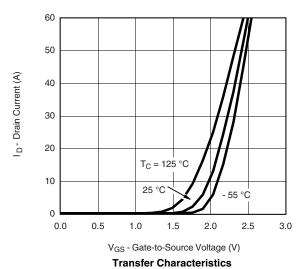
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted









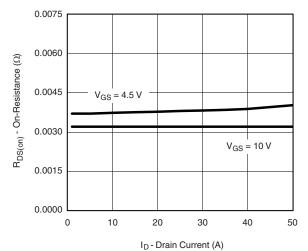
V_{GS} - Gate-to-Source Voltage (V)

I_S - Source Current (A)

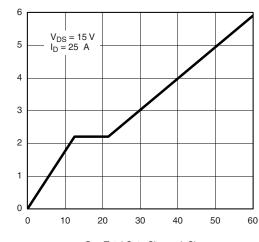
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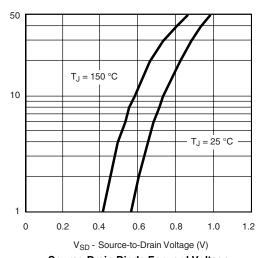
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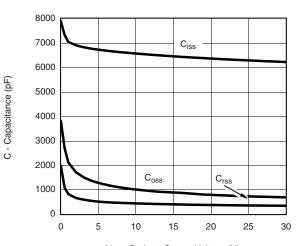
On-Resistance vs. Drain Current



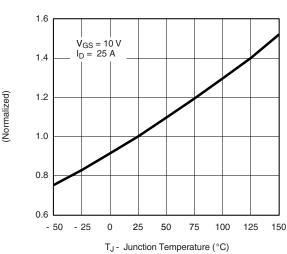
Q_g - Total Gate Charge (nC) **Gate Charge**



Source-Drain Diode Forward Voltage

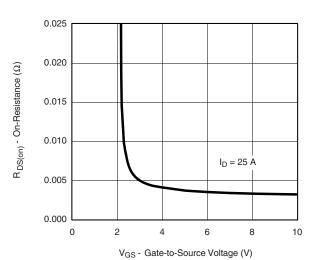


V_{DS} - Drain-to-Source Voltage (V) Capacitance



R_{DS(on)} - On-Resistance

On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage

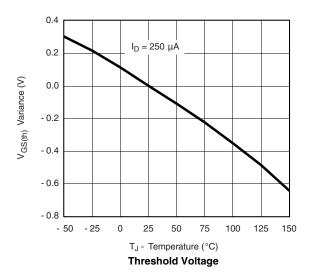


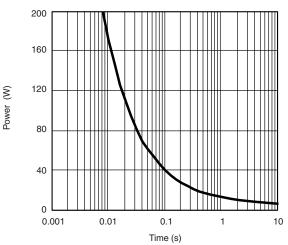
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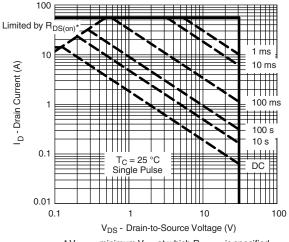
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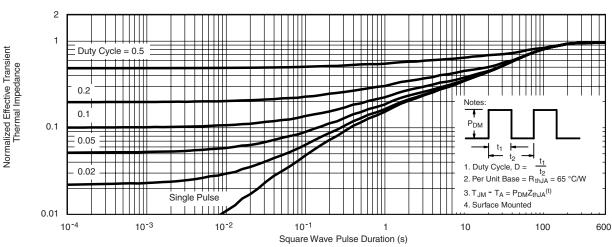




Single Pulse Power, Junction-to-Ambient



* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified Safe Operating Area, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Ambient

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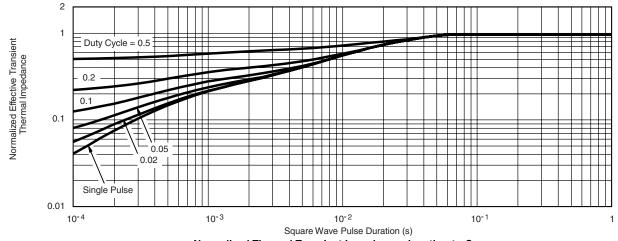
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?73156.

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